

SEMiX302GB066HDs



SEMiX[®] 2s

Trench IGBT Modules

SEMiX302GB066HDs

Features

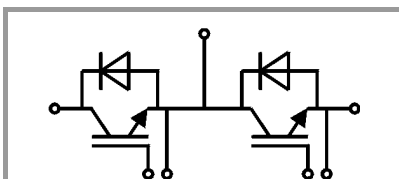
- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- UL recognised file no. E63532

Typical Applications*

- Matrix Converter
- Resonant Inverter
- Current Source Inverter

Remarks

- Case temperature limited to $T_C=125^\circ\text{C}$ max.
- Product reliability results are valid for $T_J=150^\circ\text{C}$
- For short circuit: Soft R_{Goff} recommended
- Take care of over-voltage caused by stray inductance



GB

Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
IGBT				
V_{CES}	$T_J = 25^\circ\text{C}$		600	V
I_C	$T_J = 175^\circ\text{C}$	$T_C = 25^\circ\text{C}$	379	A
		$T_C = 80^\circ\text{C}$	286	A
I_{Cnom}			300	A
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$		600	A
V_{GES}			-20 ... 20	V
t_{psc}	$V_{CC} = 360\text{ V}$ $V_{GE} \leq 15\text{ V}$ $T_J = 150^\circ\text{C}$ $V_{CES} \leq 600\text{ V}$		6	μs
T_J			-40 ... 175	$^\circ\text{C}$
Inverse diode				
I_F	$T_J = 175^\circ\text{C}$	$T_C = 25^\circ\text{C}$	419	A
		$T_C = 80^\circ\text{C}$	307	A
I_{Fnom}			300	A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$		600	A
I_{FSM}	$t_p = 10\text{ ms, sin } 180^\circ, T_J = 25^\circ\text{C}$		1400	A
T_J			-40 ... 175	$^\circ\text{C}$
Module				
$I_t(\text{RMS})$	$T_{terminal} = 80^\circ\text{C}$		600	A
T_{stg}			-40 ... 125	$^\circ\text{C}$
V_{isol}	AC sinus 50Hz, $t = 1\text{ min}$		4000	V

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
IGBT						
$V_{CE(sat)}$	$I_C = 300\text{ A}$ $V_{GE} = 15\text{ V}$ chipllevel	$T_J = 25^\circ\text{C}$		1.45	1.85	V
		$T_J = 150^\circ\text{C}$		1.7	2.1	V
V_{CE0}		$T_J = 25^\circ\text{C}$		0.9	1	V
		$T_J = 150^\circ\text{C}$		0.85	0.9	V
r_{CE}	$V_{GE} = 15\text{ V}$	$T_J = 25^\circ\text{C}$		1.8	2.8	$\text{m}\Omega$
		$T_J = 150^\circ\text{C}$		2.8	4.0	$\text{m}\Omega$
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 4.8\text{ mA}$		5	5.8	6.5	V
I_{CES}	$V_{GE} = 0\text{ V}$ $V_{CE} = 600\text{ V}$	$T_J = 25^\circ\text{C}$		0.15	0.45	mA
		$T_J = 150^\circ\text{C}$				mA
C_{ies}	$V_{CE} = 25\text{ V}$	$f = 1\text{ MHz}$		18.5		nF
C_{oes}	$V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$		1.15		nF
C_{res}		$f = 1\text{ MHz}$		0.55		nF
Q_G	$V_{GE} = -8\text{ V} \dots +15\text{ V}$			2400		nC
R_{Gint}	$T_J = 25^\circ\text{C}$			1.00		Ω
$t_{d(on)}$	$V_{CC} = 300\text{ V}$			110		ns
t_r	$I_C = 300\text{ A}$			85		ns
E_{on}	$T_J = 150^\circ\text{C}$			11.5		mJ
$t_{d(off)}$	$R_{G on} = 5.1\ \Omega$ $R_{G off} = 5.1\ \Omega$			820		ns
t_f				70		ns
E_{off}				15		mJ
$R_{th(j-c)}$	per IGBT				0.16	K/W

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Features

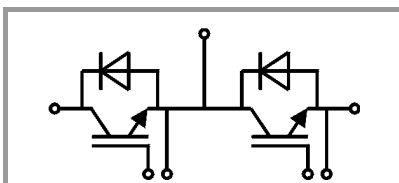
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Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
$V_F = V_{EC}$	$I_F = 300\text{ A}$ $V_{GE} = 0\text{ V}$ chip	$T_j = 25^\circ\text{C}$		1.4	1.60	V
		$T_j = 150^\circ\text{C}$		1.4	1.6	V
V_{F0}		$T_j = 25^\circ\text{C}$	0.9	1	1.1	V
		$T_j = 150^\circ\text{C}$	0.75	0.85	0.95	V
r_F		$T_j = 25^\circ\text{C}$	1.0	1.3	1.7	m Ω
		$T_j = 150^\circ\text{C}$	1.5	1.8	2.2	m Ω
I_{RRM}	$I_F = 300\text{ A}$	$T_j = 150^\circ\text{C}$		240		A
Q_{rr}	$di/dt_{off} = 3600\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$		35		μC
E_{rr}	$V_{GE} = -8\text{ V}$ $V_{CC} = 300\text{ V}$	$T_j = 150^\circ\text{C}$		7.5		mJ
$R_{th(j-c)}$	per diode				0.19	K/W
Module						
L_{CE}				18		nH
R_{CC+EE}	res., terminal-chip	$T_C = 25^\circ\text{C}$		0.7		m Ω
		$T_C = 125^\circ\text{C}$		1		m Ω
$R_{th(c-s)}$	per module			0.045		K/W
M_s	to heat sink (M5)		3		5	Nm
M_t	to terminals (M6)		2.5		5	Nm
w					250	g
Temperature sensor						
R_{100}	$T_c=100^\circ\text{C}$ ($R_{25}=5\text{ k}\Omega$)			$493 \pm 5\%$		Ω
$B_{100/125}$	$R_{(T)}=R_{100}\exp[B_{100/125}(1/T-1/T_{100})]$; T[K];			$3550 \pm 2\%$		K

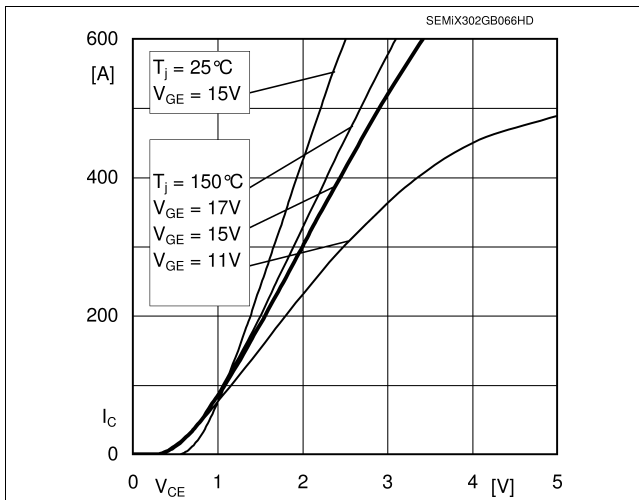


Fig. 1: Typ. output characteristic, inclusive $R_{CC'+EE'}$

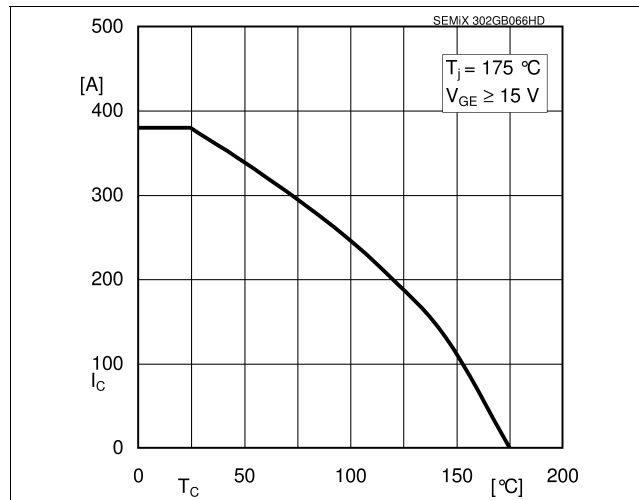


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

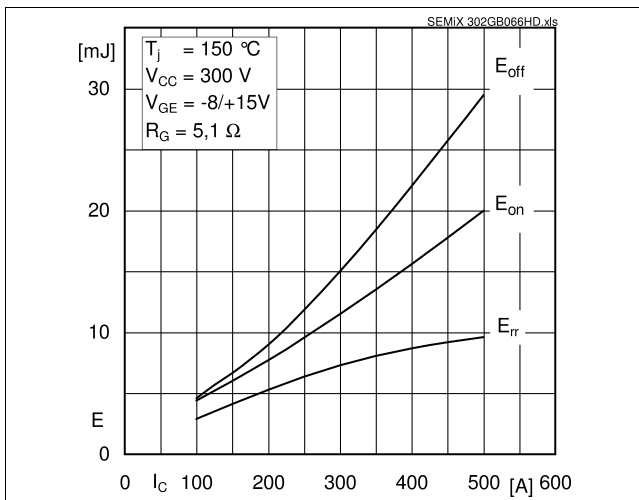


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

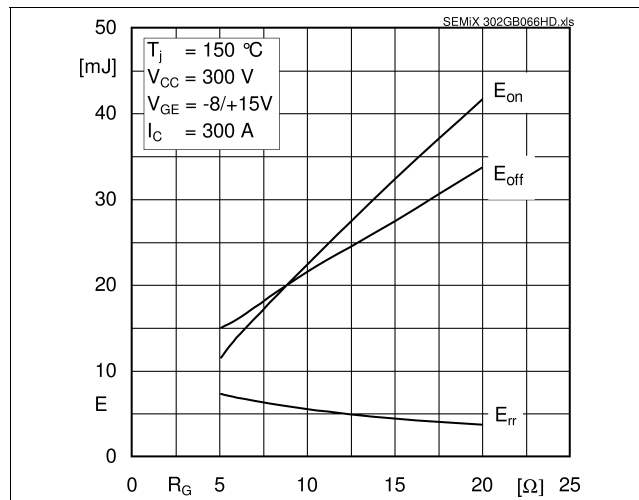


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

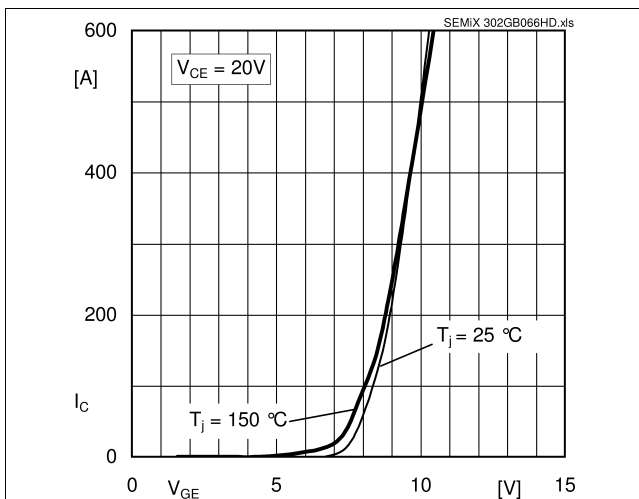


Fig. 5: Typ. transfer characteristic

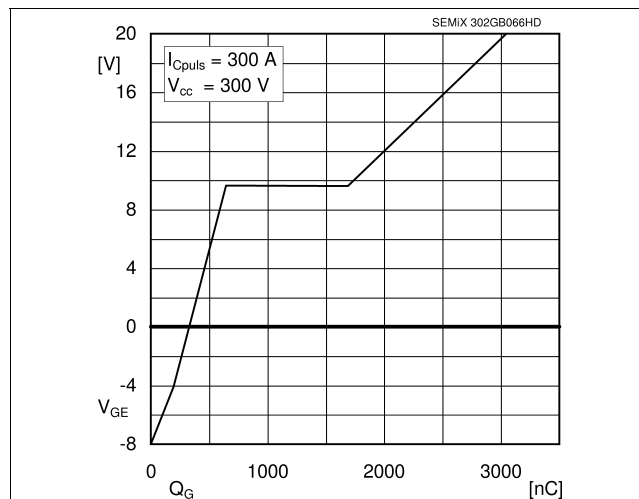


Fig. 6: Typ. gate charge characteristic

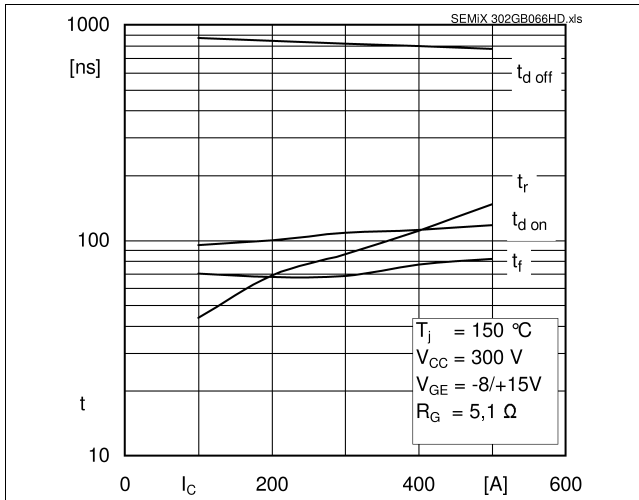


Fig. 7: Typ. switching times vs. I_C

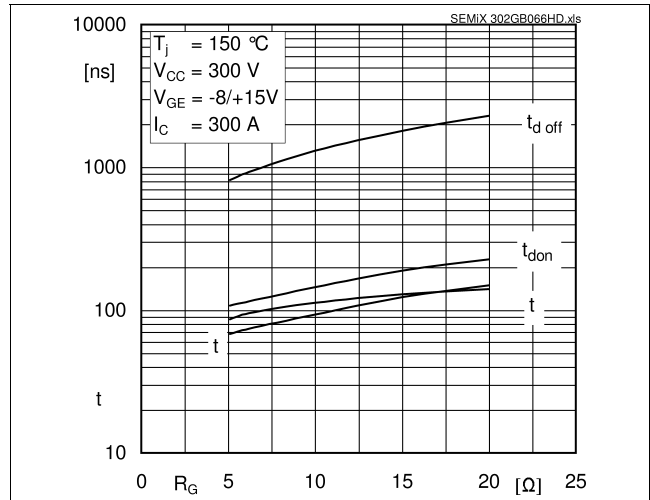


Fig. 8: Typ. switching times vs. gate resistor R_G

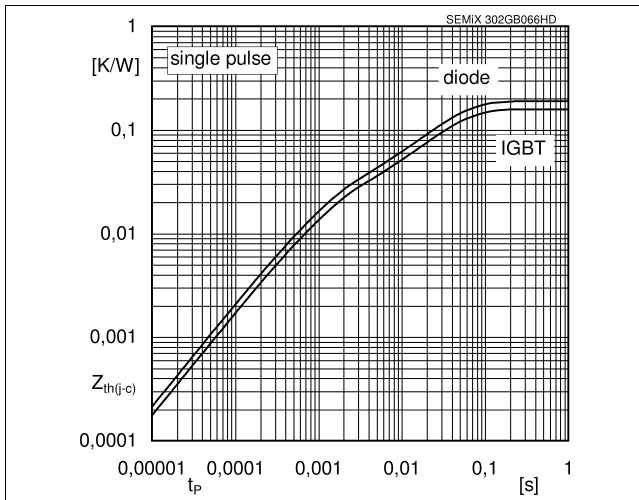


Fig. 9: Typ. transient thermal impedance

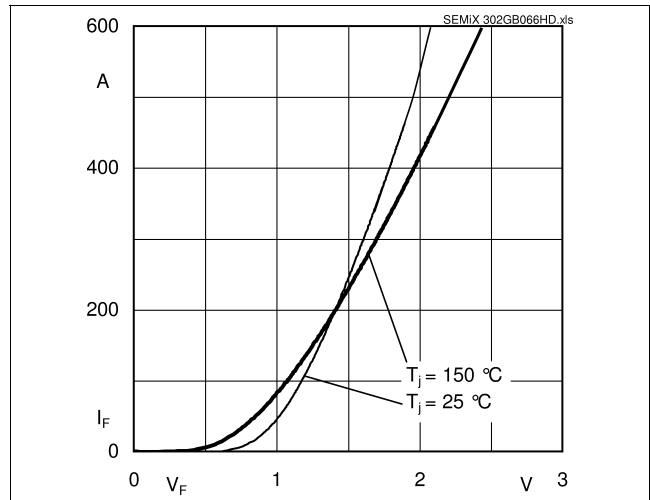


Fig. 10: Typ. CAL diode forward charact., incl. R_{CC+EE}'

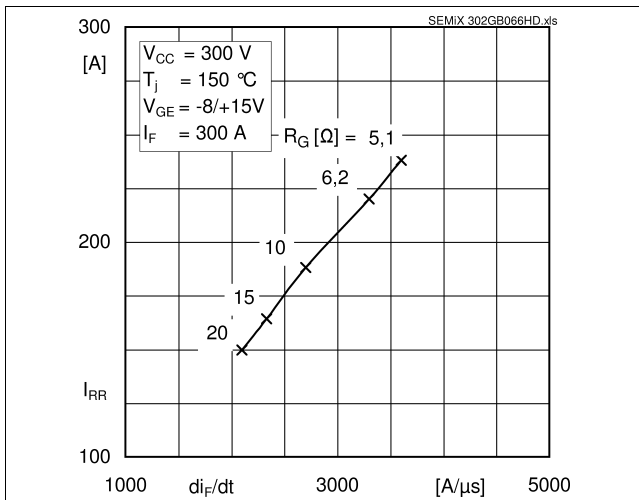


Fig. 11: Typ. CAL diode peak reverse recovery current

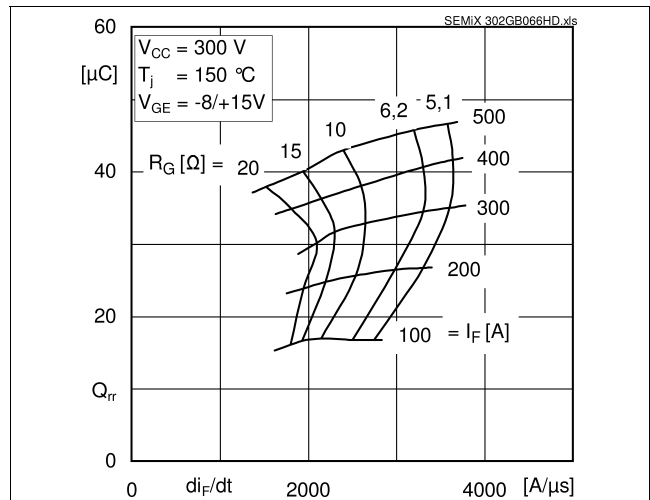
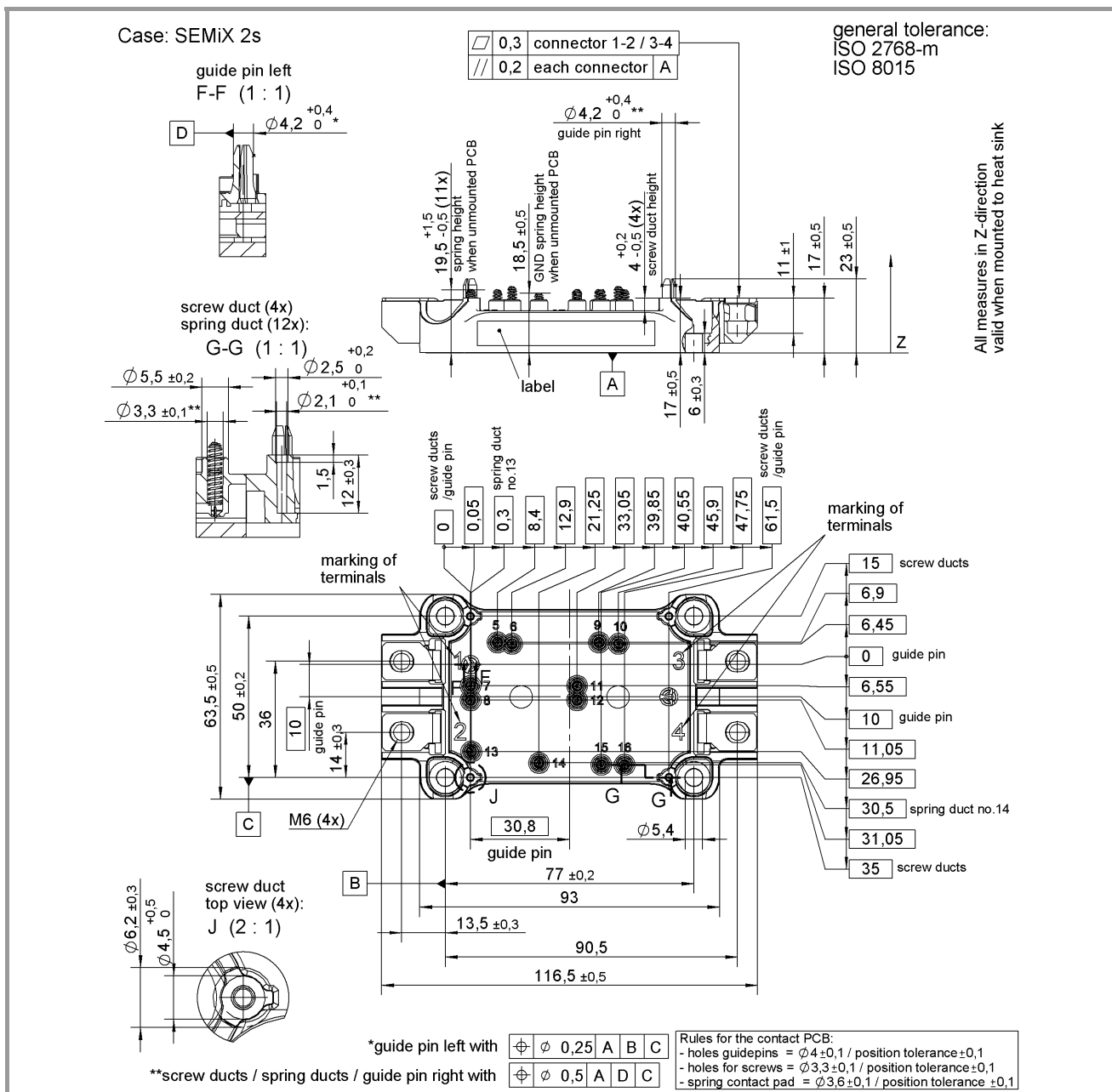
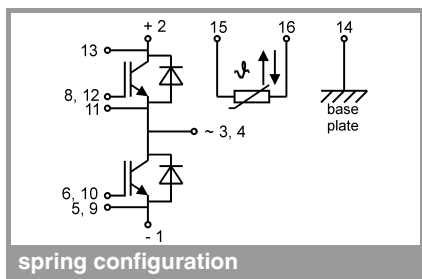


Fig. 12: Typ. CAL diode recovery charge

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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.